

# Michele Baldini

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/12091714/publications.pdf>

Version: 2024-02-01

10  
papers

1,691  
citations

1306789

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1372195

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1218  
citing authors

#	ARTICLE	IF	CITATIONS
1	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped $\beta$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	2.2	468
2	Enhancement-mode Ga <sub>2</sub> O <sub>3</sub> wrap-gate fin field-effect transistors on native (100) $\beta$ -Ga <sub>2</sub> O <sub>3</sub> substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	1.5	298
3	$\beta$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	2.2	248
4	Editors' Choice "Si- and Sn-Doped Homoepitaxial $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Layers Grown by MOVPE on (010)-Oriented Substrates. ECS Journal of Solid State Science and Technology, 2017, 6, Q3040-Q3044.	0.9	219
5	Homoepitaxial growth of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> layers by metal-organic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 27-33.	0.8	170
6	Recent progress in the growth of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> for power electronics applications. Materials Science in Semiconductor Processing, 2018, 78, 132-146.	1.9	168
7	Semiconducting Sn-doped $\beta$ -Ga <sub>2</sub> O <sub>3</sub> homoepitaxial layers grown by metal organic vapour-phase epitaxy. Journal of Materials Science, 2016, 51, 3650-3656.	1.7	116
8	Modulation frequency dependence of the photoelectrical response of GaAs/InGaP superlattices. Journal of Applied Physics, 2009, 106, 113709.	1.1	2
9	Anomalies in the Temperature Dependence of the Photoelectrical Response of GaAs/InGaP Superlattices. Japanese Journal of Applied Physics, 2010, 49, 122001.	0.8	1
10	Vertical transport through GaAs/InGaP multi-quantum-wells p-i-n diode with evidence of tunneling effects. Journal of Applied Physics, 2011, 110, 103704.	1.1	1